

# Guanyu Zhou

## List of Publications by Year in descending order

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Version: 2024-02-01

20  
papers

838  
citations

687363  
13  
h-index

794594  
19  
g-index

20  
all docs

20  
docs citations

20  
times ranked

1707  
citing authors

#	ARTICLE	IF	CITATIONS
1	Controlled crack propagation for atomic precision handling of wafer-scale two-dimensional materials. <i>Science</i> , 2018, 362, 665-670.	12.6	208
2	Ultrafast Dynamics Evidence of High Temperature Superconductivity in Single Unit Cell FeSe on $\text{SrTiO}_3$ . <i>Physical Review Letters</i> , 2016, 116, 107001.	7.8	77
3	Origin of charge transfer and enhanced electron-phonon coupling in single unit-cell FeSe films on $\text{SrTiO}_3$ . <i>Nature Communications</i> , 2017, 8, 214.	12.8	77
4	High-Mobility Helical Tellurium Field-Effect Transistors Enabled by Transfer-Free, Low-Temperature Direct Growth. <i>Advanced Materials</i> , 2018, 30, e1803109.	21.0	71
5	Interface-enhanced electron-phonon coupling and high-temperature superconductivity in potassium-coated ultrathin FeSe films on $\text{SrTiO}_3$ . <i>Physical Review B</i> , 2016, 93, 320501.	3.2	70
6	Interface induced high temperature superconductivity in single unit-cell FeSe on $\text{SrTiO}_3(110)$ . <i>Applied Physics Letters</i> , 2016, 108, .	3.3	51
7	Atomically resolved FeSe/ $\text{SrTiO}_3$ interface structure by scanning transmission electron microscopy. <i>2D Materials</i> , 2016, 3, 024002.	4.4	50
8	Interface-enhanced high-temperature superconductivity in single-unit-cell $\text{FeTe}_{0.5}\text{S}_{0.5}$ films. <i>Physical Review B</i> , 2013, 88, 134508.	3.2	48
9	Superconductivity dichotomy in K-coated single and double unit cell FeSe films on $\text{SrTiO}_3$ . <i>Physical Review B</i> , 2015, 92, .	3.2	47
10	Wetting layer evolution and its temperature dependence during self-assembly of InAs/GaAs quantum dots. <i>Nanoscale Research Letters</i> , 2012, 7, 600.	5.7	31
11	Interface enhanced superconductivity in monolayer FeSe films on MgO(001): charge transfer with atomic substitution. <i>Science Bulletin</i> , 2018, 63, 747-752.	9.0	24
12	WSe <sub>2</sub> -Te alloys grown by molecular beam epitaxy. <i>2D Materials</i> , 2019, 6, 045027.	4.4	20
13	Carrier tunneling effects on the temperature dependent photoluminescence of InAs/GaAs quantum dot: Simulation and experiment. <i>Journal of Applied Physics</i> , 2011, 109, 083501.	2.5	17
14	Temperature dependent photoluminescence of an In(Ga)As/GaAs quantum dot system with different areal density. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 295401.	2.8	12
15	Controlling the Pd Metal Contact Polarity to Trigonal Tellurium by Atomic Hydrogen Removal of the Native Tellurium Oxide. <i>Advanced Materials Interfaces</i> , 2021, 8, 2002050.	3.7	10
16	Superconductivity above 28 K in single unit cell FeSe films interfaced with $\text{GaO}_2$ layer on $\text{NdGaO}_3(1\text{-}1\text{-}0)$ . <i>Science Bulletin</i> , 2019, 64, 490-494.	9.0	8
17	The two- to three-dimensional growth transition of InAs/GaAs epitaxy layer studied by reflectance difference spectroscopy. <i>Journal of Applied Physics</i> , 2010, 108, 083513.	2.5	7
18	The transition from two-stage to three-stage evolution of wetting layer of InAs/GaAs quantum dots caused by postgrowth annealing. <i>Applied Physics Letters</i> , 2011, 98, 071914.	3.3	6

#	ARTICLE	IF	CITATIONS
19	Asymmetrically optimized structure in a high- <i>T</i> <sub>c</sub> single unit-cell FeSe superconductor. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 055701.	1.8	4
20	Effects of ultra-low Al alloying In(Al)As layer on the formation and evolution of InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 2011, 109, 094311.	2.5	0